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2/12/03  
PATENT  
465-758P  
*John H*

**IN THE U.S. PATENT AND TRADEMARK OFFICE**

Applicant: Jun S. LEE Conf.: 5244  
Serial No.: 09/722,583 Art Unit: 2823  
Filed: November 28, 2000 Examiner: B. Kebede  
For: METHOD FOR FABRICATING CAPACITOR OF  
SEMICONDUCTOR DEVICE

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TECHNOLOGY CENTER 2800

**AMENDMENT UNDER 37 C.F.R. §1.111**

Assistant Commissioner for Patents  
Washington, DC 20231

February 5, 2003

Sir:

In response to the Office Action mailed November 7, 2002 (Paper No. 14),  
the following amendments and remarks are respectfully submitted in

connection with the above-identified application:  
02/12/2003 ASH/TH 0000007 0244  
01 FC:1201 84.00 CH

**IN THE CLAIMS:**

Please **rewrite claims 1 and 4** as follows:

1. (Amended) A method for fabricating a capacitor of a semiconductor  
device comprising:

depositing a nitride film and an oxide film over a substrate, the oxide film  
being deposited on the nitride film by chemical vapor deposition;

sequentially etching the oxide film and the nitride film using a patterned  
photoresist as a mask;

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*E<sub>1</sub>*